





Please see attached Response to Restriction Requirement and Amendment.

No. 2486 P. I TIPROFESSIONAL CORPORATION

Date: May 15, 2003

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PTO/SB/21 (6-99)
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Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number. 10/053,138 **Application Number** 01/18/2002 Filing Date TRANSMITTAL Savas First Named Inventor **FORM** 1763 (to be used for all correspondence after initial filing) Group/Art Unit Parviz Hassanzadeh Examiner Name 14912.786 Attorney Docket Number Total Number of Pages in This Submission 10 ENCLOSURES (check all that apply) After Allowance Communication Assignment Papers Fee Transmittal Form to Group (for an Application) Appeal Communication to Board Drawing(s) Fee Attached of Appeals and Interferences Appeal Communication to Group Licensing-related Papers Amendment / Response (Appeal Notice, Brief, Reply Brief) Petition Routing Slip (PTO/SB/69) Proprietary Information After Final and Accompanying Petition Version with Markings Showing Petition to Convert to a Status Letter Changes Provisional Application Additional Enclosure(s) Power of Attorney, Revocation Affidavits/declaration(s) (please identify below): Change of Correspondence Address Extension of Time Request Terminal Disclaimer Information Disclosure Statement Small Entity Statement Certified Copy of Priority Request for Refund Document(s) Response to Missing Parts/ Remarks Incomplete Application Response to Missing Parts under 37 CFR 1.52 or 1.53 SIGNATURE OF APPLICANT, ATTORNEY OR AGENT Firm Michael J. Murphy, Reg. No. 37,404, WILSON SONSINI GOODRICH & ROSATI Individual name Signature Customer Number: 021971 Date CERTIFICATE OF FACSIMILE TRANSMISSION I hereby certify that this correspondence is being transmitted to the Commissioner for Patents, Washington, D.C. FAX: 703.872.9310 20231, on this date: May 15, 2003 Typed or printed name Linda Faye

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May 15, 2003

Date

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PATENT Attorney Docket No. 14912.786

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Stephen E. Savas

Application No.: 10/053,138

Filed:

01/18/2002

For:

Pulsed Plasma Processing of Semiconductor)

Substrates

Oloup Alt Omt. 1705

Examiner: Parviz Hassanzadeh

#5A

## RESPONSE TO RESTRICTION REQUIREMENT AND AMENDMENT

Mail Stop: Amendment Commissioner for Patents

PO Box 1450

Alexandria VA 22313-1450

Please consider the following amendments and remarks prior to commencing examination of this application.

In the Claims

Claims 1-43, canceled herein.

44. (Original) A method of plasma processing a semiconductor substrate,

comprising:

providing a processing chamber for processing the semiconductor substrate using a plasma;

inductively coupling power to the plasma via a first power source using high power cycles and low power cycles such that greater than about 5kW of power is coupled to the plasma during each high power cycle;